

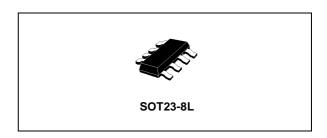
## **DUAL BUS BUFFER (3-STATE)**

- HIGH SPEED:  $t_{PD} = 3.8 \text{ns}$  (TYP.) at  $V_{CC} = 5 \text{V}$
- LOW POWER DISSIPATION:  $I_{CC} = 1\mu A(MAX.)$  at  $T_A = 25$ °C
- COMPATIBLE WITH TTL OUTPUTS: V<sub>IH</sub> = 2V (MIN), V<sub>IL</sub> = 0.8V (MAX)
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: |I<sub>OH</sub>| = I<sub>OL</sub> = 8mA (MIN)
- BALANCED PROPAGATION DELAYS:  $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE: V<sub>CC</sub>(OPR) = 4.5V to 5.5V
- IMPROVED LATCH-UP IMMUNITY

#### **DESCRIPTION**

The 74V2T126 is an advanced high-speed CMOS DUAL BUS BUFFER fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

3-STATE control input nG has to be set LOW to place the output into the high impedance state.



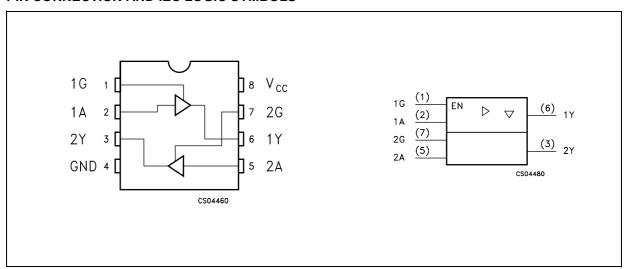
#### **ORDER CODES**

PACKAGE	T & R				
SOT23-8L	74V2T126STR				

Power down protection is provided on all inputs and outputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 3V to 5V systems and it is ideal for portable applications like personal digital assistant, camcorder and all battery-powered equipment.

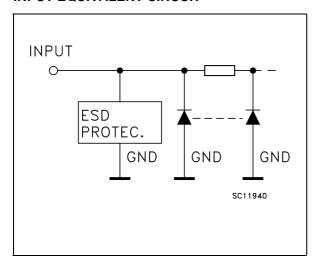
All inputs and outputs are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS



June 2003 1/8

#### **INPUT EQUIVALENT CIRCUIT**



#### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 7	1G, 2G	Output Enable Inputs
2, 5	1A, 2A	Data Inputs
3, 6	2Y, 1Y	Data Outputs
4	GND	Ground (0V)
8	V <sub>CC</sub>	Positive Supply Voltage

#### **TRUTH TABLE**

nA	nG	nY
X	L	Z
L	Н	L
Н	Н	Н

X: "H" or "L"
Z: High Impedance

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	- 20	mA
Io	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	4.5 to 5.5	V
$V_{I}$	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) ( $V_{CC} = 5.0 \pm 0.5V$ )	0 to 20	ns/V

1) V<sub>IN</sub> from 0.8V to 2V

### **DC SPECIFICATION**

		1	est Condition	Value							
Symbol	Parameter	v <sub>cc</sub>		Т	A = 25°	C	-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input Voltage	4.5 to 5.5		2.0			2.0		2.0		٧
V <sub>IL</sub>	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V <sub>OH</sub>	High Level Output	4.5	I <sub>O</sub> =-50 μA	4.4	4.5		4.4		4.4		V
	Voltage	4.5	I <sub>O</sub> =-8 mA	3.94			3.8		3.7		V
$V_{OL}$	Low Level Output	4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
	Voltage	4.5	I <sub>O</sub> =8 mA			0.36		0.44		0.55	V
I <sub>OZ</sub>	High Impedance Output Leakage Current	5.5	$V_I = V_{IH}$ or $V_{IL}$ $V_O = 5.5$ or GND			±0.25		± 2.5		± 5	μΑ
I <sub>I</sub>	Input Leakage Current	0 to 5.5	V <sub>I</sub> = 5.5V or GND			± 0.1		± 1		± 1	μΑ
I <sub>OPD</sub>	Power down Output Leakage Current	0	V <sub>O</sub> = 5.5			0.5		5		10	μΑ
I <sub>CC</sub>	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μΑ
△I <sub>CC</sub>	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V <sub>CC</sub> or GND			1.35		1.5		1.5	mA

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$ )

	Test Condition			Value								
Symbol Parameter		v <sub>cc</sub>	CL	Cı		T <sub>A</sub> = 25°C			85°C	-55 to 125°C		Unit
		(V)	(pF)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t <sub>PLH</sub>	Propagation Delay	5.0 <sup>(*)</sup>	15			3.8	5.5	1.0	6.5	1.0	7.5	
t <sub>PHL</sub>	Time	5.0 <sup>(*)</sup>	50			4.3	6.5	1.0	7.5	1.0	8.5	
t <sub>PLZ</sub>	Output Disable	5.0 <sup>(*)</sup>	15	$R_L = 1 \text{ K}\Omega$		3.6	5.0	1.0	6.0	1.0	7.0	no
t <sub>PHZ</sub>	Time	5.0 <sup>(*)</sup>	50	$R_L = 1 K\Omega$		5.1	7.0	1.0	8.0	1.0	9.0	ns
t <sub>PZL</sub>	Output Enable	5.0 <sup>(*)</sup>	15	$R_L = 1 K\Omega$		3.7	5.9	1.0	7.0	1.0	8.0	
t <sub>PZH</sub>	Time	5.0 <sup>(*)</sup>	50	$R_L = 1 K\Omega$		4.1	6.5	1.0	7.5	1.0	8.5	

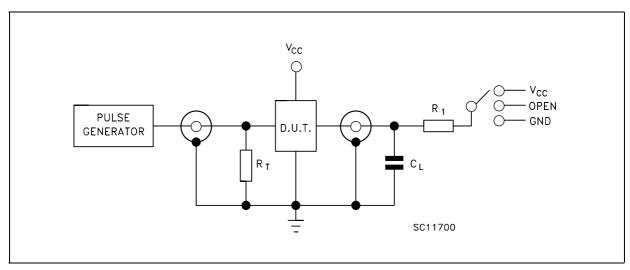
<sup>(\*)</sup> Voltage range is 5.0V ± 0.5V

#### **CAPACITIVE CHARACTERISTICS**

		Test Condition		Value						
Symbol	Parameter		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance			4	10		10		10	pF
C <sub>OUT</sub>	Output Capacitance			6						pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)			14						pF

<sup>1)</sup>  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/2$ 

#### **TEST CIRCUIT TEST CIRCUIT**



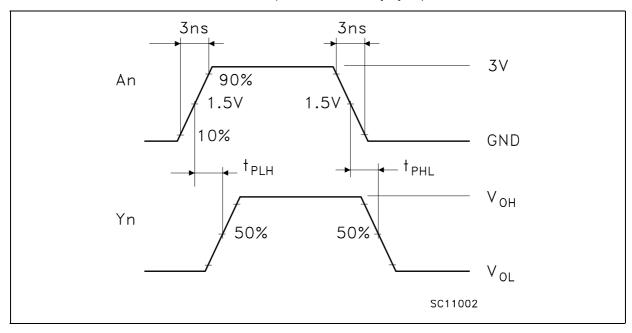
TEST	SWITCH
t <sub>PLH</sub> , t <sub>PHL</sub>	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	V <sub>CC</sub>
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND

 $C_L$  =15/50pF or equivalent (includes jig and probe capacitance)

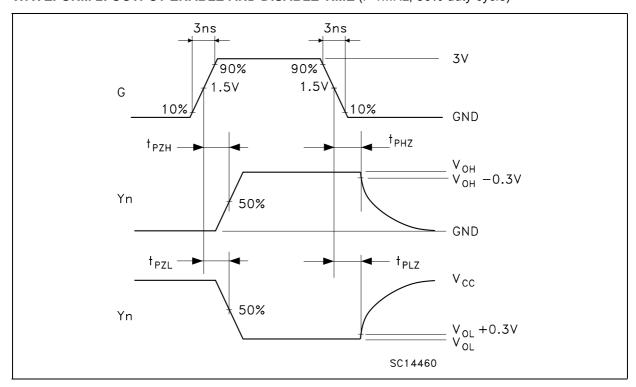
 $R1 = 1K\Omega$  or equivalent

 $R_T = Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )

### WAVEFORM 1: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)

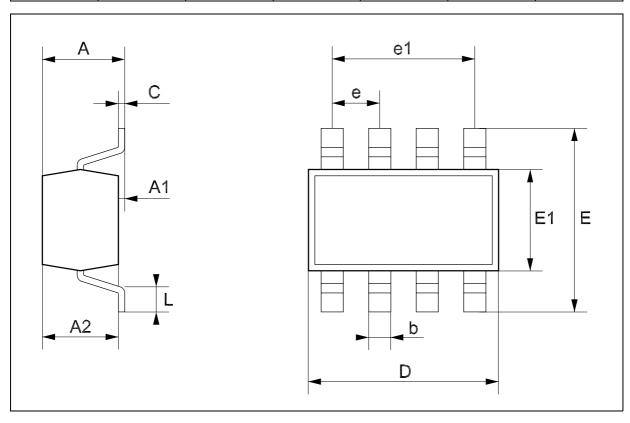


## WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME (f=1MHz; 50% duty cycle)



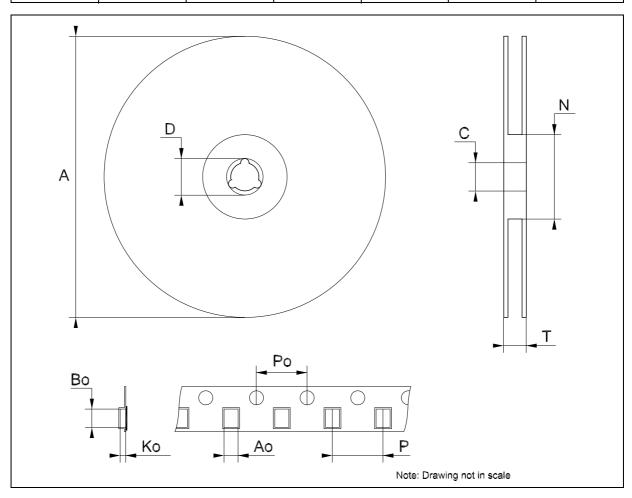
## **SOT23-8L MECHANICAL DATA**

DIM		mm.		mils				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А	0.90		1.45	35.4		57.1		
A1	0.00		0.15	0.0		5.9		
A2	0.90		1.30	35.4		51.2		
b	0.22		0.38	8.6		14.9		
С	0.09		0.20	3.5		7.8		
D	2.80		3.00	110.2		118.1		
E	2.60		3.00	102.3		118.1		
E1	1.50		1.75	59.0		68.8		
е	0	.65			25.6			
e1		1.95			76.7			
L	0.35		0.55	13.7		21.6		



# Tape & Reel SOT23-xL MECHANICAL DATA

DIM		mm.		inch					
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
А			180			7.086			
С	12.8	13.0	13.2	0.504	0.512	0.519			
D	20.2			0.795					
N	60			2.362					
Т			14.4			0.567			
Ao	3.13	3.23	3.33	0.123	0.127	0.131			
Во	3.07	3.17	3.27	0.120	0.124	0.128			
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58			
Po	3.9	4.0	4.1	0.153	0.157	0.161			
Р	3.9	4.0	4.1	0.153	0.157	0.161			



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47/ 8/8